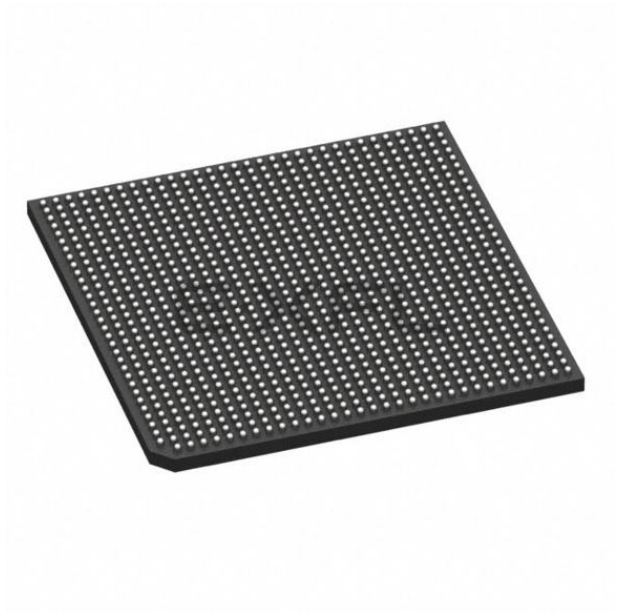

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.2GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.5V, 1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	1023-BFBGA, FCBGA
Supplier Device Package	1023-FCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8572eclpxatld

the upper and lower words of the 64-bit GPRs as they are defined by the SPE APU.

— Embedded vector and scalar single-precision floating-point APUs. Provide an instruction set for single-precision (32-bit) floating-point instructions.

— Double-precision floating-point APU. Provides an instruction set for double-precision (64-bit) floating-point instructions that use the 64-bit GPRs.

— 36-bit real addressing

— Memory management unit (MMU). Especially designed for embedded applications. Supports 4-Kbyte to 4-Gbyte page sizes.

— Enhanced hardware and software debug support

— Performance monitor facility that is similar to, but separate from, the MPC8572E performance monitor

The e500 defines features that are not implemented on this device. It also generally defines some features that this device implements more specifically. An understanding of these differences can be critical to ensure proper operation.

- 1 Mbyte L2 cache/SRAM
  — Shared by both cores.
  — Flexible configuration and individually configurable per core.
  — Full ECC support on 64-bit boundary in both cache and SRAM modes
  — Cache mode supports instruction caching, data caching, or both.
  — External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing).
    – 1, 2, or 4 ways can be configured for stashing only.
  — Eight-way set-associative cache organization (32-byte cache lines)
  — Supports locking entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions.
  — Global locking and Flash clearing done through writes to L2 configuration registers
  — Instruction and data locks can be Flash cleared separately.
  — Per-way allocation of cache region to a given processor.
  — SRAM features include the following:
    – 1, 2, 4, or 8 ways can be configured as SRAM.
    – I/O devices access SRAM regions by marking transactions as snoopable (global).
    – Regions can reside at any aligned location in the memory map.
    – Byte-accessible ECC is protected using read-modify-write transaction accesses for smaller-than-cache-line accesses.
- e500 coherency module (ECM) manages core and intrasystem transactions
- Address translation and mapping unit (ATMU)
  — Twelve local access windows define mapping within local 36-bit address space.
  — Inbound and outbound ATMUs map to larger external address spaces.

- Supports fully nested interrupt delivery
- Interrupts can be routed to external pin for external processing.
- Interrupts can be routed to the e500 core's standard or critical interrupt inputs.
- Interrupt summary registers allow fast identification of interrupt source.

- Integrated security engine (SEC) optimized to process all the algorithms associated with IPSec, IKE, SSL/TLS, SRTP, 802.16e, and 3GPP
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Dynamic assignment of crypto-execution units through an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - PKEU—public key execution unit
    - RSA and Diffie-Hellman; programmable field size up to 4096 bits
    - Elliptic curve cryptography with F_2m and F(p) modes and programmable field size up to 1023 bits
  - DEU—Data Encryption Standard execution unit
    - DES, 3DES
    - Two key (K1, K2, K1) or three key (K1, K2, K3)
    - ECB, CBC and OFB-64 modes for both DES and 3DES
  - AESU—Advanced Encryption Standard unit
    - Implements the Rijndael symmetric key cipher
    - ECB, CBC, CTR, CCM, GCM, CMAC, OFB-128, CFB-128, and LRW modes
    - 128-, 192-, and 256-bit key lengths
  - AFEU—ARC four execution unit
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - MDEU—message digest execution unit
    - SHA-1 with 160-bit message digest
    - SHA-2 (SHA-256, SHA-384, SHA-512)
    - MD5 with 128-bit message digest
    - HMAC with all algorithms
  - KEU—Kasumi execution unit
    - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
    - Also supports A5/3 and GEA-3 algorithms
  - RNG—random number generator
  - XOR engine for parity checking in RAID storage applications
  - CRC execution unit
    - CRC-32 and CRC-32C
- Pattern Matching Engine with DEFLATE decompression

NOTE

From a system standpoint, if any of the I/O power supplies ramp prior to the VDD core supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-on reset, and extra current may be drawn by the device.

3 Power Characteristics

The estimated typical power dissipation for the core complex bus (CCB) versus the core frequency for this family of PowerQUICC III devices with out the L in its part ordering is shown in Table 4.

Table 4. MPC8572E Power Dissipation [1]

CCB Frequency	Core Frequency	Typical-65[2]	Typical-105[3]	Maximum[4]	Unit
533	1067	12.3	17.8	18.5	W
533	1200	12.3	17.8	18.5	W
533	1333	16.3	22.8	24.5	W
600	1500	17.3	23.9	25.9	W

Notes:

1. This reflects the MPC8572E power dissipation excluding the power dissipation from B/G/L/O/T/XV_{DD} rails.
2. Typical-65 is based on V_{DD} = 1.1 V, T_j = 65 °C, running Dhrystone.
3. Typical-105 is based on V_{DD} = 1.1 V, T_j = 105 °C, running Dhrystone.
4. Maximum is based on V_{DD} = 1.1 V, T_j = 105 °C, running a smoke test.

The estimated typical power dissipation for the core complex bus (CCB) versus the core frequency for this family of PowerQUICC III devices with the L in its port ordering is shown in Table 5.

Table 5. MPC8572EL Power Dissipation [1]

CCB Frequency	Core Frequency	Typical-65[2]	Typical-105[3]	Maximum[4]	Unit
533	1067	12	15	15.8	W
533	1200	12	15.5	16.3	W
533	1333	12	15.9	16.9	W
600	1500	13	18.7	20.0	W

Notes:

1. This reflects the MPC8572E power dissipation excluding the power dissipation from B/G/L/O/T/XV_{DD} rails.
2. Typical-65 is based on V_{DD} = 1.1 V, T_j = 65 °C, running Dhrystone.
3. Typical-105 is based on V_{DD} = 1.1 V, T_j = 105 °C, running Dhrystone.
4. Maximum is based on V_{DD} = 1.1 V, T_j = 105 °C, running a smoke test.

4 Input Clocks

4.1 System Clock Timing

Table 6 provides the system clock (SYSCLK) AC timing specifications for the MPC8572E.

Table 6. SYSCLK AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3V ± 5%.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	33	—	133	MHz	1
SYSCLK cycle time	t_{SYSCLK}	7.5	—	30.3	ns	—
SYSCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t_{KHK}/t_{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	+/– 150	ps	4, 5, 6

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies.Refer to Section 19.2, “CCB/SYSCLK PLL Ratio,” and Section 19.3, “e500 Core PLL Ratio,” for ratio settings.
2. Rise and fall times for SYSCLK are measured at 0.6 V and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The SYSCLK driver’s closed loop jitter bandwidth should be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYSCLK drivers with the specified jitter.
6. For spread spectrum clocking, guidelines are +0% to –1% down spread at a modulation rate between 20 kHz and 60 kHz on SYSCLK.

4.2 Real Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal should be greater than 2x the period of the CCB clock. That is, minimum clock high time is $2 \times t_{CCB}$, and minimum clock low time is $2 \times t_{CCB}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

Table 9. RESET Initialization Timing Specifications (continued)

PLL config input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	µs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Notes:
1. SYSCLK is the primary clock input for the MPC8572E.
2. Reset assertion timing requirements for DDR3 DRAMs may differ.

Table 10 provides the PLL lock times.

Table 10. PLL Lock Times

Parameter/Condition	Symbol	Min	Typical	Max
PLL lock times	—	100	µs	—
Local bus PLL	—	50	µs	—

6 DDR2 and DDR3 SDRAM Controller

This section describes the DC and AC electrical specifications for the DDR2 and DDR3 SDRAM controller interface of the MPC8572E. Note that the required GV_{DD}(typ) voltage is 1.8Vor 1.5 V when interfacing to DDR2 or DDR3 SDRAM, respectively.

6.1 DDR2 and DDR3 SDRAM Interface DC Electrical Characteristics

Table 11 provides the recommended operating conditions for the DDR SDRAM controller of the MPC8572E when interfacing to DDR2 SDRAM.

Table 11. DDR2 SDRAM Interface DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	$MV_{REF}n$	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF}n - 0.04$	$MV_{REF}n + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF}n + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF}n - 0.125$	V	—
Output leakage current	I_{OZ}	–50	50	µA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—

Table 11. DDR2 SDRAM Interface DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. $MV_{REF}n$ is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to that far end signal termination is made and is expected to be equal to $MV_{REF}n$. This rail should track variations in the DC level of $MV_{REF}n$.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 12 provides the recommended operating conditions for the DDR SDRAM controller of the MPC8572E when interfacing to DDR3 SDRAM.

Table 12. DDR3 SDRAM Interface DC Electrical Characteristics for GV_{DD}(typ) = 1.5 V

Parameter/Condition	Symbol	Min	Typical	Max	Unit
I/O supply voltage	GV_{DD}	1.425	1.575	V	1
I/O reference voltage	$MV_{REF}n$	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
Input high voltage	V_{IH}	$MV_{REF}n$ + 0.100	GV_{DD}	V	—
Input low voltage	V_{IL}	GND	$MV_{REF}n$ – 0.100	V	—
Output leakage current	I_{OZ}	–50	50	µA	3

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. $MV_{REF}n$ is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed ±1% of the DC value.
3. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 13 provides the DDR SDRAM controller interface capacitance for DDR2 and DDR3.

Table 13. DDR2 and DDR3 SDRAM Interface Capacitance for GV_{DD}(typ)=1.8 V and 1.5 V

Parameter/Condition	Symbol	Min	Typical	Max	Unit
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1, 2
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1, 2

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V (for DDR2), f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.
2. This parameter is sampled. GV_{DD} = 1.5 V ± 0.075 V (for DDR3), f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.175 V.

The Fast Ethernet Controller (FEC) operates in MII mode only, and complies with the AC and DC electrical characteristics specified in this chapter for MII. Note that if FEC is used, eTSEC 3 and 4 are only available in SGMII mode.

8.1.1 eTSEC DC Electrical Characteristics

All MII, GMII, RMII, and TBI drivers and receivers comply with the DC parametric attributes specified in Table 23 and Table 24. All RGMII, RTBI and FIFO drivers and receivers comply with the DC parametric attributes specified in Table 24. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 23. GMII, MII, RMII, and TBI DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD} TV_{DD}	3.13	3.47	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, IOH = –4.0 mA)	VOH	2.40	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, IOL = 4.0 mA)	VOL	GND	0.50	V	—
Input high voltage	V_{IH}	2.0	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	40	µA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–600	—	µA	3

Notes:

1 LV_{DD} supports eTSECs 1 and 2.
2 TV_{DD} supports eTSECs 3 and 4 or FEC.
3 The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1.

Table 24. MII, GMII, RMII, RGMII, TBI, RTBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.37	2.63	V	1,2
Output high voltage (LV_{DD}/TV_{DD} = Min, IOH = –1.0 mA)	V_{OH}	2.00	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	GND – 0.3	0.40	V	—
Input high voltage	V_{IH}	1.70	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.70	V	—

Table 24. MII, GMII, RMII, RGMII, TBI, RTBI, and FIFO DC Electrical Characteristics (continued)

Parameters	Symbol	Min	Max	Unit	Notes
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	10	µA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–15	—	µA	3

Note:

1 LV_{DD} supports eTSECs 1 and 2.
2 TV_{DD} supports eTSECs 3 and 4 or FEC.
3 Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1.

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, because they have similar performance and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC*n*'s TSEC*n*_TX_CLK, while the receive clock must be applied to pin TSEC*n*_RX_CLK. The eTSEC internally uses the transmit clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back on the TSEC*n*_GTX_CLK pin (while transmit data appears on TSEC*n*_TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSEC*n*_GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, because the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is a relationship between the maximum FIFO speed and the platform (CCB) frequency. For more information see Section 4.5, "Platform to eTSEC FIFO Restrictions."

Table 25 and Table 26 summarize the FIFO AC specifications.

Table 25. FIFO Mode Transmit AC Timing Specification

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5V ± 5%

Parameter/Condition	Symbol	Min	Typ	Max	Unit
TX_CLK, GTX_CLK clock period[1]	t_{FIT}	5.3	8.0	100	ns
TX_CLK, GTX_CLK duty cycle	t_{FITH}/t_{FIT}	45	50	55	%

Table 36. RMII Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5/ 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RXD[1:0], CRS_DV, RX_ER hold time to TSECn_TX_CLK rising edge	t_{RMRDX}	2.0	—	—	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 20 provides the AC test load for eTSEC.

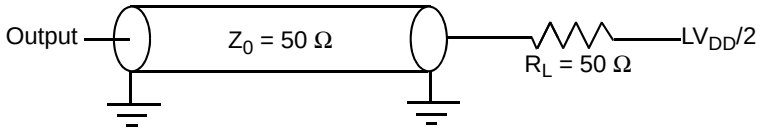


Figure 20. eTSEC AC Test Load

Figure 21 shows the RMII receive AC timing diagram.

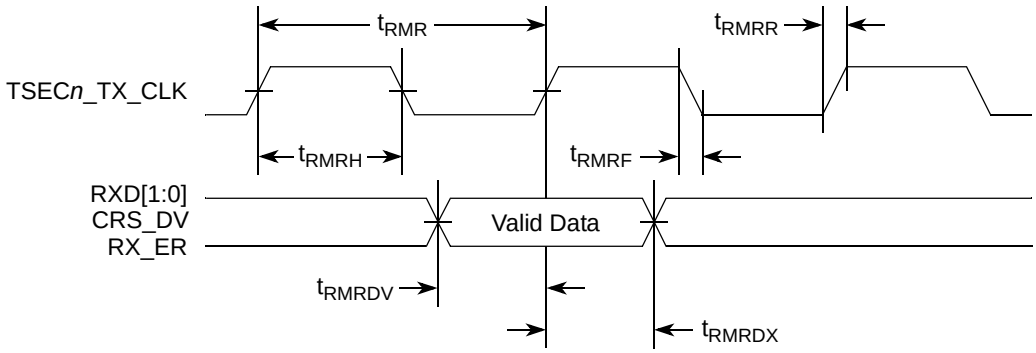


Figure 21. RMII Receive AC Timing Diagram

8.3 SGMII Interface Electrical Characteristics

Each SGMII port features a 4-wire AC-Coupled serial link from the dedicated SerDes 2 interface of MPC8572E as shown in Figure 22, where C_{TX} is the external (on board) AC-Coupled capacitor. Each output pin of the SerDes transmitter differential pair features 50-Ω output impedance. Each input of the SerDes receiver differential pair features 50-Ω on-die termination to SGND_SRDS2 (xcorevss). The reference circuit of the SerDes transmitter and receiver is shown in Figure 54.

When an eTSEC port is configured to operate in SGMII mode, the parallel interface's output signals of this eTSEC port can be left floating. The input signals should be terminated based on the guidelines

Table 42. eTSEC IEEE 1588 AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/TV_{DD} of 3.3 V ± 5% or 2.5 V ± 5%

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Note
TSEC_1588_CLK_OUT duty cycle	$t_{T1588CLKOTH}$ /$t_{T1588CLKOUT}$	30	50	70	%	—
TSEC_1588_PULSE_OUT	$t_{T1588OV}$	0.5	—	3.0	ns	—
TSEC_1588_TRIG_IN pulse width	$t_{T1588TRIGH}$	$2*t_{T1588CLK\_MAX}$	—	—	ns	2

Note:

1. When TMR_CTRL[CKSEL] is set as '00', the external TSEC_1588_CLK input is selected as the 1588 timer reference clock source, with the timing defined in Table 42, "eTSEC IEEE 1588 AC Timing Specifications." The maximum value of $t_{T1588CLK}$ is defined in terms of T_{TX_CLK}, that is the maximum clock cycle period of the equivalent interface speed that the eTSEC1 port is running at. When eTSEC1 is configured to operate in the parallel mode, the T_{TX_CLK} is the maximum clock period of the TSEC1_TX_CLK. When eTSEC1 operates in SGMII mode, the maximum value of $t_{T1588CLK}$ is defined in terms of the recovered clock from SGMII SerDes. For example, for SGMII 10/100/1000 Mbps modes, the maximum value of $t_{T1588CLK}$ is 3600, 360, 72 ns respectively. See the *MPC8572E PowerQUICC™ III Integrated Communications Processor Reference Manual* for detailed description of TMR_CTRL registers.
2. It needs to be at least two times of the clock period of the clock selected by TMR_CTRL[CKSEL].

9 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals ECn_MDIO (management data input/output) and ECn_MDC (management data clock). The electrical characteristics for GMII, SGMII, RGMII, RMII, TBI and RTBI are specified in "Section 8, "Ethernet: Enhanced Three-Speed Ethernet (eTSEC)."

9.1 MII Management DC Electrical Characteristics

The ECn_MDC and ECn_MDIO are defined to operate at a supply voltage of 3.3 V or 2.5 V. The DC electrical characteristics for ECn_MDIO and ECn_MDC are provided in Table 43 and Table 44.

Table 43. MII Management DC Electrical Characteristics (LV_{DD}/TV_{DD}=3.3 V)

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage (3.3 V)	LV_{DD}/TV_{DD}	3.13	3.47	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.10	OV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} =Min, I_{OL} = 1.0 mA)	V_{OL}	GND	0.50	V	—
Input high voltage	V_{IH}	2.0	—	V	—
Input low voltage	V_{IL}	—	0.90	V	—
Input high current (LV_{DD}/TV_{DD} = Max, V_{IN} [3] = 2.1 V)	I_{IH}	—	40	µA	—

Table 52. Local Bus General Timing Parameters—PLL Bypassed (continued)

At recommended operating conditions with BV_{DD} of 3.3 V ± 5%

Parameter	Symbol [1]	Min	Max	Unit	Notes
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKL2}$	-1.3	—	ns	4, 5
LALE output negation to high impedance for LAD/LDP (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKLOV1}$	—	–0.3	ns	
Local bus clock to data valid for LAD/LDP	$t_{LBKLOV2}$	—	–0.1	ns	4
Local bus clock to address valid for LAD	$t_{LBKLOV3}$	—	0.0	ns	4
Local bus clock to LALE assertion	$t_{LBKLOV4}$	—	0.0	ns	4
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKLOX1}$	–3.3	—	ns	4
Output hold from local bus clock for LAD/LDP	$t_{LBKLOX2}$	–3.3	—	ns	4
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKLOZ1}$	—	0.2	ns	7
Local bus clock to output high impedance for LAD/LDP	$t_{LBKLOZ2}$	—	0.2	ns	7

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to local bus clock for PLL bypass mode. Timings may be negative with respect to the local bus clock because the actual launch and capture of signals is done with the internal launch/capture clock, which precedes LCLK by t_{LBKHKT}.
3. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.
4. All signals are measured from BVDD/2 of the rising edge of local bus clock for PLL bypass mode to 0.4 x BVDD of the signal in question for 3.3-V signaling levels.
5. Input timings are measured at the pin.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

NOTE

In PLL bypass mode, LCLK[n] is the inverted version of the internal clock with the delay of t_{LBKHKT}. In this mode, signals are launched at the rising edge of the internal clock and are captured at the falling edge of the internal clock with the exception of $\overline{\text{LGTA}}$/LUPWAIT (which is captured on the rising edge of the internal clock).

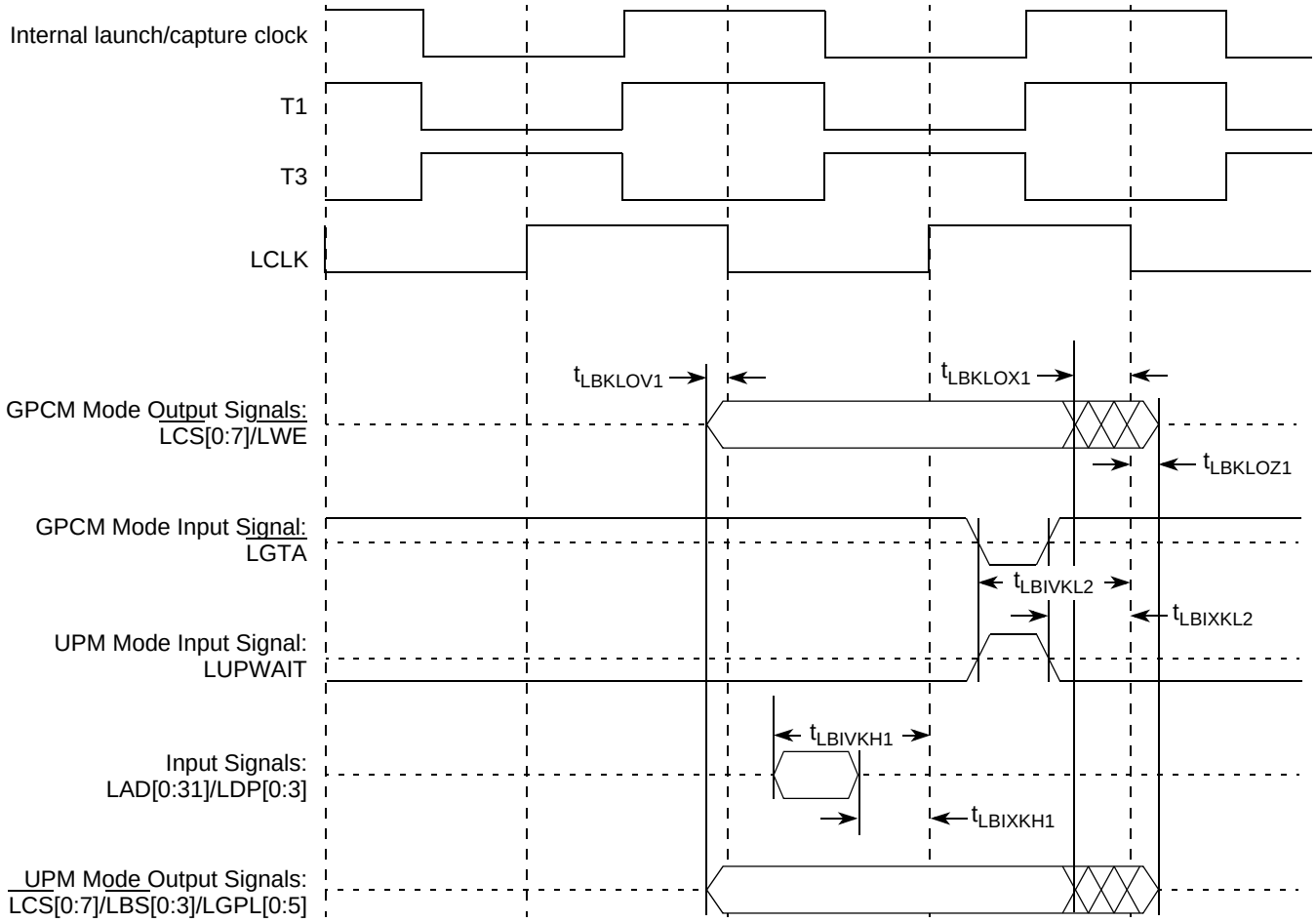


Figure 33. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (PLL Bypass Mode)

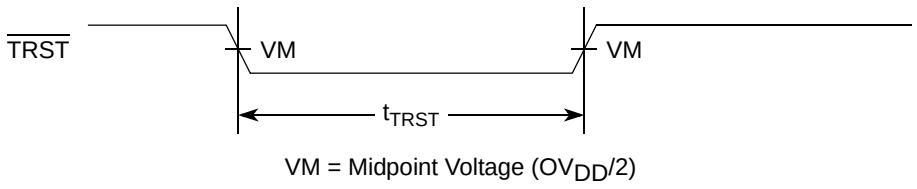


Figure 38. $\overline{\text{TRST}}$ Timing Diagram

Figure 39 provides the boundary-scan timing diagram.

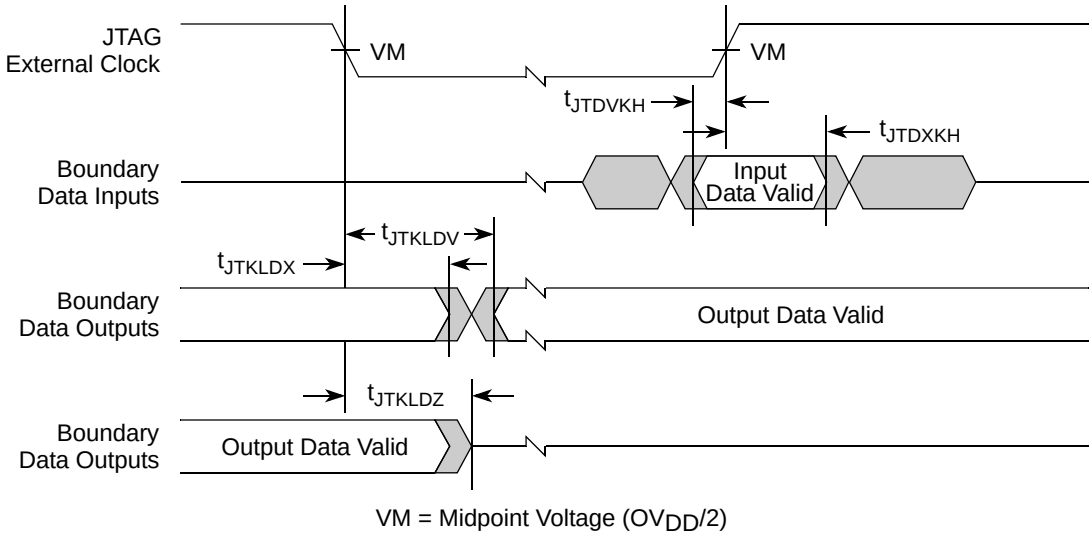


Figure 39. Boundary-Scan Timing Diagram

13 I²C

This section describes the DC and AC electrical characteristics for the I²C interfaces of the MPC8572E.

13.1 I²C DC Electrical Characteristics

Table 54 provides the DC electrical characteristics for the I²C interfaces.

Table 54. I²C DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	0.4	V	1
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	µA	3

15 High-Speed Serial Interfaces (HSSI)

The MPC8572E features two Serializer/Deserializer (SerDes) interfaces to be used for high-speed serial interconnect applications. The SerDes1 interface can be used for PCI Express and/or Serial RapidIO data transfers. The SerDes2 is dedicated for SGMII application.

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes Reference Clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

15.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 43 shows how the signals are defined. For illustration purpose, only one SerDes lane is used for description. The figure shows waveform for either a transmitter output (SDn_TX and $\overline{\text{SDn\_TX}}$) or a receiver input (SDn_RX and $\overline{\text{SDn\_RX}}$). Each signal swings between A Volts and B Volts where A > B.

Using this waveform, the definitions are as follows. To simplify illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

1. **Single-Ended Swing**

   The transmitter output signals and the receiver input signals SDn_TX, $\overline{\text{SDn\_TX}}$, SDn_RX and $\overline{\text{SDn\_RX}}$ each have a peak-to-peak swing of A - B Volts. This is also referred as each signal wire's Single-Ended Swing.

2. **Differential Output Voltage, V_{OD}** (or **Differential Output Swing**):

   The Differential Output Voltage (or Swing) of the transmitter, V_{OD}, is defined as the difference of the two complimentary output voltages: $V_{SDn\_TX} - V_{\overline{SDn\_TX}}$. The V_{OD} value can be either positive or negative.

3. **Differential Input Voltage, V_{ID}** (or **Differential Input Swing**):

   The Differential Input Voltage (or Swing) of the receiver, V_{ID}, is defined as the difference of the two complimentary input voltages: $V_{SDn\_RX} - V_{\overline{SDn\_RX}}$. The V_{ID} value can be either positive or negative.

4. **Differential Peak Voltage, V_{DIFFp}**

   The peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak Voltage, $V_{DIFFp} = |A - B|$ Volts.

5. **Differential Peak-to-Peak, $V_{DIFFp-p}$**

   Because the differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) Volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak-to-Peak Voltage, $V_{DIFFp-p} = 2*V_{DIFFp} = 2 * |(A - B)|$ Volts, which is twice of differential swing in amplitude, or twice of the differential peak. For example, the output differential peak-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2*|V_{OD}|$.

Table 66. Short Run Transmitter AC Timing Specifications—2.5 GBaud (continued)

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Multiple Output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	400	400	ps	+/- 100 ppm

Table 67. Short Run Transmitter AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output Voltage,	V_O	–0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V_{DIFFPP}	500	1000	mV p-p	—
Deterministic Jitter	J_D	—	0.17	UI p-p	—
Total Jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	320	320	ps	+/– 100 ppm

Table 68. Long Run Transmitter AC Timing Specifications—1.25 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output Voltage,	V_O	–0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V_{DIFFPP}	800	1600	mV p-p	—
Deterministic Jitter	J_D	—	0.17	UI p-p	—
Total Jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	800	800	ps	+/- 100 ppm

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{D1\_MCAS}}$	Column Address Strobe	AC9	O	GV_{DD}	—
$\overline{\text{D1\_MRAS}}$	Row Address Strobe	AB12	O	GV_{DD}	—
D1_MCKE[0:3]	Clock Enable	M8, L9, T9, N8	O	GV_{DD}	11
$\overline{\text{D1\_MCS}}$[0:3]	Chip Select	AB9, AF10, AB11, AE11	O	GV_{DD}	—
D1_MCK[0:5]	Clock	V7, E13, AH11, Y9, F14, AG10	O	GV_{DD}	—
$\overline{\text{D1\_MCK}}$[0:5]	Clock Complements	Y10, E12, AH12, AA11, F13, AG11	O	GV_{DD}	—
D1_MODT[0:3]	On Die Termination	AD10, AF12, AC10, AE12	O	GV_{DD}	—
D1_MDIC[0:1]	Driver Impedance Calibration	E15, G14	I/O	GV_{DD}	25
DDR SDRAM Memory Interface 2					
D2_MDQ[0:63]	Data	A6, B7, C5, D5, A7, C8, D8, D6, C4, A3, D3, D2, B4, A4, B1, C1, E3, E1, G2, G6, D1, E4, G5, G3, J4, J2, P4, R5, H3, H1, N5, N3, Y6, Y4, AC3, AD2, V5, W5, AB2, AB3, AD5, AE3, AF6, AG7, AC4, AD4, AF4, AF7, AH5, AJ1, AL2, AM3, AH3, AH6, AM1, AL3, AK5, AL5, AJ7, AK7, AK4, AM4, AL6, AM7	I/O	GV_{DD}	—
D2_MECC[0:7]	Error Correcting Code	J5, H7, L7, N6, H4, H6, M4, M5	I/O	GV_{DD}	—
$\overline{\text{D2\_MAPAR\_ERR}}$	Address Parity Error	N1	I	GV_{DD}	—
D2_MAPAR_OUT	Address Parity Out	W2	O	GV_{DD}	—
D2_MDM[0:8]	Data Mask	A5, B3, F4, J1, AA4, AE5, AK1, AM5, K5	O	GV_{DD}	—
D2_MDQS[0:8]	Data Strobe	B6, C2, F5, L4, AB5, AF3, AL1, AM6, L6	I/O	GV_{DD}	—
$\overline{\text{D2\_MDQS}}$[0:8]	Data Strobe	C7, A2, F2, K3, AA5, AE6, AK2, AJ6, K6	I/O	GV_{DD}	—
D2_MA[0:15]	Address	W1, U4, U3, T1, T2, T3, R1, R2, T5, R4, Y3, P1, N2, AF1, M2, M1	O	GV_{DD}	—

Table 76. MPC8572E Pinout Listing (continued)

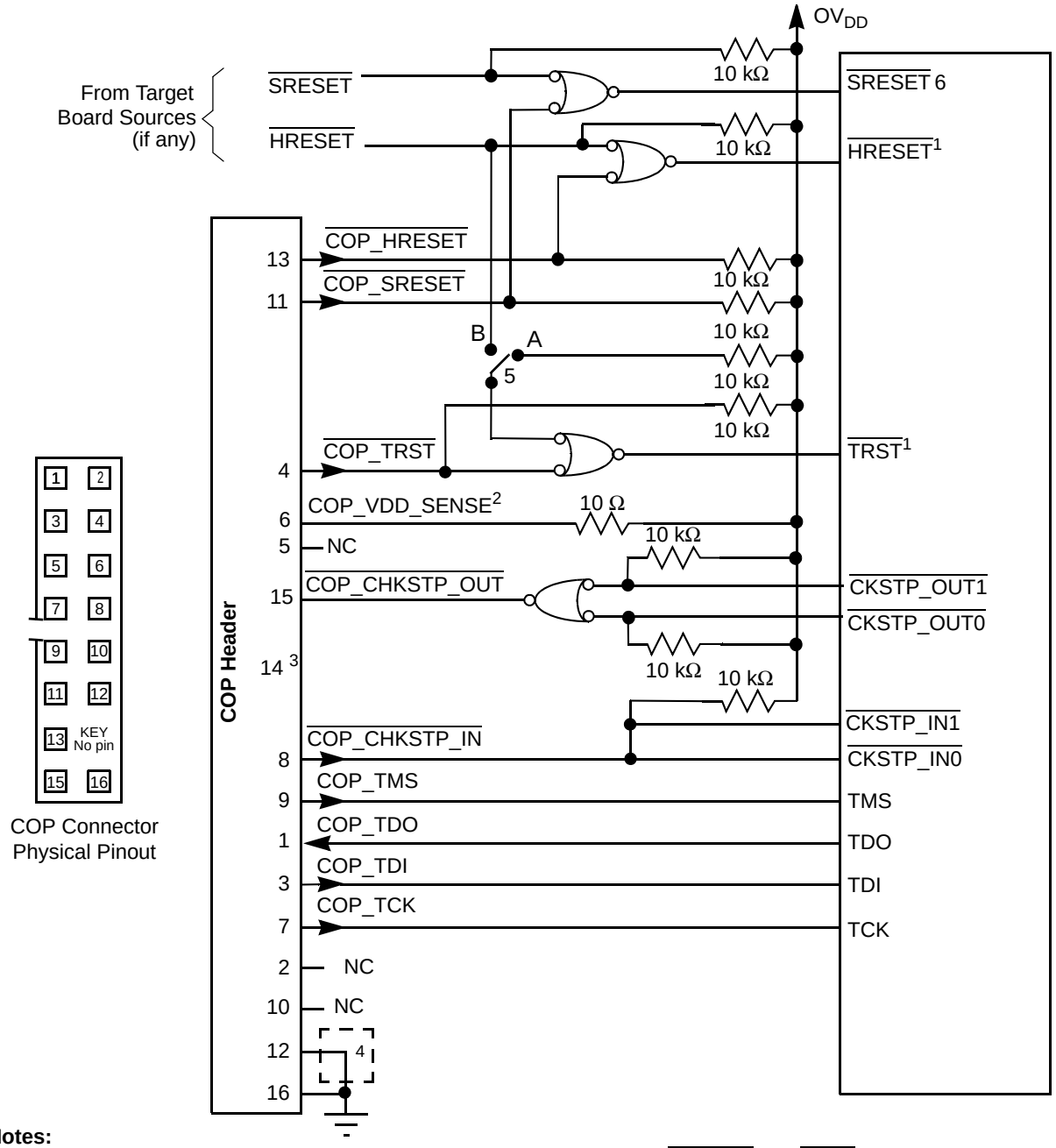
Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
SD1_RX[7:0]	Receive Data (positive)	P32, N30, M32, L30, G30, F32, E30, D32	I	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_RX}}$[7:0]	Receive Data (negative)	P31, N29, M31, L29, G29, F31, E29, D31	I	XV_{DD_SRDS1}	—
SD1_TX[7]	PCIe1 Tx Data Lane 7 / SRIO or PCIe2 Tx Data Lane 3 / PCIe3 TX Data Lane 1	M26	O	XV_{DD_SRDS1}	—
SD1_TX[6]	PCIe1 Tx Data Lane 6 / SRIO or PCIe2 Tx Data Lane 2 / PCIe3 TX Data Lane 0	L24	O	XV_{DD_SRDS1}	—
SD1_TX[5]	PCIe1 Tx Data Lane 5 / SRIO or PCIe2 Tx Data Lane 1	K26	O	XV_{DD_SRDS1}	—
SD1_TX[4]	PCIe1 Tx Data Lane 4 / SRIO or PCIe2 Tx Data Lane 0	J24	O	XV_{DD_SRDS1}	—
SD1_TX[3]	PCIe1 Tx Data Lane 3	G24	O	XV_{DD_SRDS1}	—
SD1_TX[2]	PCIe1 Tx Data Lane 2	F26	O	XV_{DD_SRDS1}	—
SD1_TX[1]	PCIe1 Tx Data Lane 1]	E24	O	XV_{DD_SRDS1}	—
SD1_TX[0]	PCIe1 Tx Data Lane 0	D26	O	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_TX}}$[7:0]	Transmit Data (negative)	M27, L25, K27, J25, G25, F27, E25, D27	O	XV_{DD_SRDS1}	—
SD1_PLL_TPD	PLL Test Point Digital	J32	O	XV_{DD_SRDS1}	17
SD1_REF_CLK	PLL Reference Clock	H32	I	XV_{DD_SRDS1}	—
$\overline{\text{SD1\_REF\_CLK}}$	PLL Reference Clock Complement	H31	I	XV_{DD_SRDS1}	—
Reserved	—	C29, K32	—	—	26
Reserved	—	C30, K31	—	—	27
Reserved	—	C24, C25, H26, H27	—	—	28
Reserved	—	AL20, AL21	—	—	29
SerDes (x4) SGMII					
SD2_RX[3:0]	Receive Data (positive)	AK32, AJ30, AF30, AE32	I	XV_{DD_SRDS2}	—

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
Power and Ground Signals					
GND	Ground	A18, A25, A29, C3, C6, C9, C12, C15, C20, C22, E5, E8, E11, E14, F3, G7, G10, G13, G16, H5, H21, J3, J9, J12, J18, K7, L5, L13, L15, L16, L21, M3, M9, M12, M14, M16, M18, N7, N13, N15, N17, N19, N21, N23, P5, P12, P14, P16, P20, P22, R3, R9, R11, R13, R15, R17, R19, R21, R23, R26, T7, T12, T14, T16, T18, T20, T22, T30, U5, U11, U13, U15, U16, U17, U19, U21, U23, U25, V3, V9, V12, V14, V16, V18, V20, V22, W7, W11, W13, W15, W17, W19, W21, W27, W32, Y5, Y12, Y14, Y16, Y18, Y20, AA3, AA9, AA13, AA15, AA17, AA19, AA21, AA30, AB7, AB26, AC5, AC11, AC13, AD3, AD9, AD14, AD17, AD22, AE7, AE13, AF5, AF11, AG3, AG9, AG15, AG19, AH7, AH13, AH22, AJ5, AJ11, AJ17, AK3, AK9, AK15, AK24, AL7, AL13, AL19, AL26	—	—	—
XGND_SRDS1	SerDes Transceiver Pad GND (xpadvss)	C23, C27, D23, D25, E23, E26, F23, F24, G23, G27, H23, H25, J23, J26, K23, K24, L27, M25	—	—	—
XGND_SRDS2	SerDes Transceiver Pad GND (xpadvss)	AD23, AD25, AE23, AE27, AF23, AF24, AG23, AG26, AH23, AH25, AJ27	—	—	—

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
VDD	Core, L2, Logic Supply	L14, M13, M15, M17, N12, N14, N16, N20, N22, P11, P13, P15, P17, P19, P21, P23, R12, R14, R16, R18, R20, R22, T13, T15, T19, T21, T23, U12, U14, U18, U20, U22, V13, V15, V17, V19, V21, W12, W14, W16, W18, W20, W22, Y13, Y15, Y17, Y19, Y21, AA12, AA14, AA16, AA18, AA20, AB13	—	VDD	—
SVDD_SRDS1	SerDes Core 1 Logic Supply (xcorevdd)	C31, D29, E28, E32, F30, G28, G31, H29, K30, L31, M29, N32, P30	—	—	—
SVDD_SRDS2	SerDes Core 2 Logic Supply (xcorevdd)	AD32, AF31, AG29, AJ32, AK29, AK30	—	—	—
XVDD_SRDS1	SerDes1 Transceiver Supply (xpadvdd)	C26, D24, E27, F25, G26, H24, J27, K25, L26, M24, N27	—	—	—
XVDD_SRDS2	SerDes2 Transceiver Supply (xpadvdd)	AD24, AD28, AE26, AF25, AG27, AH24, AJ26	—	—	—
AVDD_LBIU	Local Bus PLL Supply	A19	—	—	19
AVDD_DDR	DDR PLL Supply	AM20	—	—	19
AVDD_CORE0	CPU PLL Supply	B18	—	—	19
AVDD_CORE1	CPU PLL Supply	A17	—	—	19
AVDD_PLAT	Platform PLL Supply	AB32	—	—	19
AVDD_SRDS1	SerDes1 PLL Supply	J29	—	—	19
AVDD_SRDS2	SerDes2 PLL Supply	AH29	—	—	19
SENSEVDD	VDD Sensing Pin	N18	—	—	13
SENSEVSS	GND Sensing Pin	P18	—	—	13
Analog Signals					
MVREF1	SSTL_1.8 Reference Voltage	C16	I	$GV_{DD}/2$	—
MVREF2	SSTL_1.8 Reference Voltage	AM19	I	$GV_{DD}/2$	—



Notes:

1. The COP port and target board should be able to independently assert $\overline{\text{HRESET}}$ and $\overline{\text{TRST}}$ to the processor to fully control the processor as shown here.
2. Populate this with a 10 Ω resistor for short-circuit/current-limiting protection.
3. The KEY location (pin 14) is not physically present on the COP header.
4. Although pin 12 is defined as a No-Connect, some debug tools may use pin 12 as an additional GND pin for improved signal integrity.
5. This switch is included as a precaution for BSDL testing. The switch should be closed to position A during BSDL testing to avoid accidentally asserting the TRST line. If BSDL testing is not being performed, this switch should be closed to position B.
6. Asserting $\overline{\text{SRESET}}$ causes a machine check interrupt to the e500 cores.